

## STATUS OF CLAIMS

Claims 1 -5 (canceled)

6. (original) A method of manufacturing the micro inertia sensor comprising the steps of:

forming a device wafer by forming a lower silicon on a lower glass substrate; etching the lower silicon for forming a side movement sensing structure including a structure being movable in a horizontal direction on the lower silicon and an sensing electrode for sensing a variation of a capacity as the structure horizontally moves, a first fixed point, and a first border for bonding; etching the lower glass substrate as a sacrificial layer; and separately evaporating Au for bonding on the lower silicon layer;

forming a cap wafer by forming an upper silicon on an upper glass substrate; forming a gap in the upper silicon; forming an second fixed point, an second border and a second sensing electrode, which correspond to the first fixed point, the first border and the structure movable in a horizontal direction in the device wafer process; and forming the via hole from an upper glass substrate to the second fixed point; and

bonding the device wafer and the cap wafer by a eutectic bonding; evaporating an electric conduction layer on the via hole to form an electric conduction wiring.

Claims 7-14 (canceled).